| L Number | Hits | Search Text | DB | Time stamp |
|---|---|---|---|---|
| 1 | 2 | ("5955772").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/06 14:34 |
| - | 1293 | (AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") | USPAT | 2001/10/09 15:41 |
| - | 1605 | (AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/16 16:52 |
| - | 743 | ((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As")) and 257/$ | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/16 11:17 |
| - | 672 | (quantum adj well photo adj excit$5 photoexcit$5) and ((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As")) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/16 11:23 |
| - | 331 | (((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As")) and 257/$) and ((quantum adj well photo adj excit$5 photoexcit$5) and ((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As"))) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/16 11:23 |
| - | 17 | (quantum adj well) and (photo adj excit$5 photoexcit$5) and ((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As")) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/16 11:24 |
| - | 0 | ((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with (barrier)) and ((("Ga As" "GaAs" GaAs) with (substrate and storage)) and ((InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") with (quantum well)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/16 11:32 |
| - | 0 | ((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with (barrier buffer)) and ((("Ga As" "GaAs" GaAs) with (substrate and storage)) and ((InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") with (quantum well)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/16 11:44 |
| - | 7 | ((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") same (barrier buffer)) and ((("Ga As" "GaAs" GaAs) same (substrate and storage)) and ((InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") same (quantum well)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/16 11:44 |
| - | 112 | ((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with (barrier buffer)) and ((("Ga As" "GaAs" GaAs) with (substrate and (quantum storage))) and ((InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") with (quantum well)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/16 11:54 |

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|---|---|---|---|---|
| - | 66 | (((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with (barrier buffer)) and (("Ga As" "GaAs" GaAs) with (substrate and (quantum storage))) and ((InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") with (quantum well))) and 257/$ | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/16 11:54 |
| - | 180 | electromagnetic adj wave adj detector | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/16 11:55 |
| - | 0 | (((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with (barrier buffer)) and (("Ga As" "GaAs" GaAs) with (substrate and (quantum storage))) and ((InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") with (quantum well))) and (electromagnetic adj wave adj detector) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/16 11:55 |
| - | 29228 | electromagnetic adj wave | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/16 11:56 |
| - | 180 | (electromagnetic adj wave ) and (electromagnetic adj wave adj detector) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/16 11:56 |
| - | 0 | (electromagnetic adj wave ) and ((((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with (barrier buffer)) and (("Ga As" "GaAs" GaAs) with (substrate and (quantum storage))) and ((InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") with (quantum well))) and 257/$) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/16 11:56 |
| - | 6 | electromagnetic and ((((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with (barrier buffer)) and (("Ga As" "GaAs" GaAs) with (substrate and (quantum storage))) and ((InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") with (quantum well))) and 257/$) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/16 12:06 |
| - | 131 | (first and third) adj (buffer barrier) adj (layer) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/16 12:42 |
| - | 0 | ((electromagnetic adj wave ) and (electromagnetic adj wave adj detector)) and ((first and third) adj (buffer barrier) adj (layer)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/16 12:43 |
| - | 1115 | (first and third) adj (buffer barrier) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/16 12:43 |
| - | 0 | ((electromagnetic adj wave ) and (electromagnetic adj wave adj detector)) and ((first and third) adj (buffer barrier) ) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/16 12:46 |

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|---|---|---|---|---|
| -- | 1589 | (third) adj (buffer barrier) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/16 12:44 |
| - | 2 | ((electromagnetic adj wave ) and (electromagnetic adj wave adj detector)) and ((third) adj (buffer barrier) ) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/16 16:10 |
| - | 1 | ("5506418").PN. | USPAT | 2001/05/16 16:30 |
| - | 8 | 5506418.URPN. | USPAT | 2001/05/16 16:12 |
| - | 8 | electron adj storage adj layer | USPAT | 2001/05/16 16:32 |
| - | 244 | electron adj storage | USPAT | 2001/05/16 16:32 |
| - | 479 | electron near stor$3 | USPAT | 2001/05/16 16:38 |
| - | 8 | 5506418.URPN. | USPAT | 2001/05/16 16:36 |
| - | 4140 | quantum adj well | USPAT | 2001/05/16 16:38 |
| - | 15 | (electron near stor$3) and (quantum adj well) | USPAT | 2001/05/16 16:39 |
| - | 17 | 5670790.URPN. | USPAT | 2001/05/16 16:49 |
| - | 468 | (AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (sens$5 detector) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/17 08:49 |
| - | 0 | electormagnet$5 and ((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (sens$5 detector)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/17 08:47 |
| - | 74 | electromagnet$5 and ((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (sens$5 detector)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/17 08:51 |
| - | 574 | (AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (sens$5 detect$5) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/17 10:12 |
| - | 78 | electromagnet$5 and ((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (sens$5 detect$5)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/17 08:51 |
| - | 215 | (AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (photosens$5 photodetect$5) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/17 09:50 |
| - | 35 | (AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and photo adj (sens$5 detect$5) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/17 09:50 |

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|---|---|---|---|---|
| - | 228 | ((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (photosens$5 photodetect$5)) ((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and photo adj (sens$5 detect$5)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/17 09:50 |
| - | 127 | (((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (photosens$5 photodetect$5)) ((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and photo adj (sens$5 detect$5))) and 257/$ | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/17 09:53 |
| - | 0 | ((((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (photosens$5 photodetect$5)) ((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and photo adj (sens$5 detect$5))) and 257/$) and grated near3 layer | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/17 09:53 |
| - | 24 | ((((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (photosens$5 photodetect$5)) ((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and photo adj (sens$5 detect$5))) and 257/$) and graded near3 layer | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/17 10:07 |
| - | 672 | (AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsinide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with graded) and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (sens$5 detect$5) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/17 14:13 |
| - | 27 | (AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsinide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As")) and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (sens$5 detect$5) and (barrier with graded) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/17 10:20 |
| - | 30 | (AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsenide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As")) and ("Ga As" gallium adj arsenide "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (sens$5 detect$5) and (barrier with graded) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/17 10:22 |
| - | 1826 | (AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsenide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with graded) and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/17 10:24 |

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|---|---|---|---|---|
| · - | 2326 | (AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsenide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with graded) and ("Ga As" gallium adj arsenide "GaAs" GaAs) and (InGaAs GaInAs "GaInAs" "Ga In As" indium adj gallium adj arsenide gallium adj indium adj arsenide "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/17 10:27 |
| - | 601 | (((AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsinide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with graded) and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (sens$5 detect$5)) ((AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsinide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As")) and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (sens$5 detect$5) and (barrier with graded)) ((AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsenide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As")) and ("Ga As" gallium adj arsenide "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (sens$5 detect$5) and (barrier with graded)) ((AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsenide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with graded) and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") ) ((AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsenide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with graded) and ("Ga As" gallium adj arsenide "GaAs" GaAs) and (InGaAs GaInAs "GaInAs" "Ga In As" indium adj gallium adj arsenide gallium adj indium adj arsenide "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") )) and (257/$ 438/$) and (sens$5 detect$5 photo adj (sens$5 detect$5) photosens$5 photodetect$5) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/17 10:36 |

| | | 513 | (((((AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsinide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with graded) and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (sens$5 detect$5)) ((AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsinide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As")) and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (sens$5 detect$5) and (barrier with graded)) ((AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsenide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As")) and ("Ga As" gallium adj arsenide "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (sens$5 detect$5) and (barrier with graded)) ((AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsenide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with graded) and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") ) ((AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsenide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with graded) and ("Ga As" gallium adj arsenide "GaAs" GaAs) and (InGaAs GaInAs "GaInAs" "Ga In As" indium adj gallium adj arsenide gallium adj indium adj arsenide "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") )) and (257/$ 438/$) and (sens$5 detect$5 photo adj (sens$5 detect$5) photosens$5 photodetect$5)) and well | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/17 10:36 |

| | 269 | (((((AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsinide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with graded) and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (sens$5 detect$5)) ((AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsinide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As")) and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (sens$5 detect$5) and (barrier with graded)) ((AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsenide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As")) and ("Ga As" gallium adj arsenide "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (sens$5 detect$5) and (barrier with graded)) ((AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsenide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with graded) and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") ) ((AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsenide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with graded) and ("Ga As" gallium adj arsenide "GaAs" GaAs) and (InGaAs GaInAs "GaInAs" "Ga In As" indium adj gallium adj arsenide gallium adj indium adj arsenide "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") )) and (257/$ 438/$) and (sens$5 detect$5 photo adj (sens$5 detect$5) photosens$5 photodetect$5)) and well) and quantum adj well | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/17 11:25 |
| - | 12 | (("5869844") or ("5086327") or ("5187715") or ("5228777") or ("5326984") or ("5506418") or ("5677544") or ("5726500") or ("5712499") or ("5719670") or ("5684817") or ("5739949")).PN. | USPAT | 2001/05/17 10:45 |
| - | 534 | (257/17,21,185).CCLS. | USPAT | 2002/02/13 16:00 |

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|---|---|---|---|---|
| ˙- | 53 | ((((((AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsinide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with graded) and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (sens$5 detect$5)) ((AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsinide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As")) and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (sens$5 detect$5) and (barrier with graded)) ((AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsenide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As")) and ("Ga As" gallium adj arsenide "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") and (sens$5 detect$5) and (barrier with graded)) ((AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsenide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with graded) and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") ) ((AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsenide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") with graded) and ("Ga As" gallium adj arsenide "GaAs" GaAs) and (InGaAs GaInAs "GaInAs" "Ga In As" indium adj gallium adj arsenide gallium adj indium adj arsenide "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") )) and (257/$ 438/$) and (sens$5 detect$5 photo adj (sens$5 detect$5) photosens$5 photodetect$5)) and well) and quantum adj well) and (("257/17,21,185").CCLS.) | USPAT | 2001/05/17 13:59 |
| - | 214 | piezoelectric near semiconductor | USPAT | 2001/05/17 14:00 |
| - | 19 | piezoelectric near semiconductor with electric adj field | USPAT | 2001/05/17 14:03 |
| - | 601 | piezoelectric with natural adjelectric adj field | USPAT | 2001/05/17 14:04 |
| - | 601 | piezoelectric with natural adjelectric adj field with semiconductor | USPAT | 2001/05/17 14:04 |
| - | 0 | piezoelectric near semiconductor with natural adj electric adj field | USPAT | 2001/05/17 14:05 |
| - | 0 | piezoelectric with natural adj electric adj field | USPAT | 2001/05/17 14:05 |
| - | 0 | piezoelectric same natural adj electric adj field | USPAT | 2001/05/17 14:16 |
| - | 6 | natural adj electric adj field | USPAT | 2001/05/17 14:05 |
| - | 428 | (AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsenide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As")) and ("Ga As" gallium adj arsenide "GaAs" GaAs) and ("Ga In As" "GaInAs" GaInAs Indium adj gallium adj arsenide InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") with (quantum adj well) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/17 14:31 |
| - | 3 | piezoelectric adj field with quantum adj well | USPAT | 2001/05/17 14:26 |
| - | 2 | (AlGaAs GaAlAs "GaAlAs" "Ga Al As" aluminum adj gallium adj arsenide "Al Ga As" "AlGaAs" ("Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As")) and ("Ga As" gallium adj arsenide "GaAs" GaAs) and ("Ga In As" "GaInAs" GaInAs Indium adj gallium adj arsenide InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As") with (piezoelectric adj field) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/17 14:54 |
| - | 2 | (gallium adj arsenide GaAs "Ga As" "GaAs" ) with (piezoelectric adj field) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/17 16:36 |

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|---|---:|---|---|---|
| - | 2 | (("257/17,21,185").CCLS.) and (electric adj field with doped adj semiconductor) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/10/09 14:43 |
| - | 52 | electric adj field with doped adj semiconductor | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/17 16:38 |
| - | 12 | electric adj field with doped adj semiconductor adj layer$1 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/17 17:56 |
| - | 172 | ohmic adj contact$1 and (("257/17,21,185").CCLS.) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/05/17 17:57 |
| - | 8 | 5506418.URPN. | USPAT | 2001/05/18 07:54 |
| - | 1 | 5594750.URPN. | USPAT | 2001/05/18 07:57 |
| - | 3 | ("5268582" \| "5481397" \| "5506418").PN. | USPAT | 2001/05/18 07:58 |
| - | 10 | 5416338.URPN. | USPAT | 2001/05/18 08:06 |
| - | 14 | 5121181.URPN. | USPAT | 2001/05/18 08:30 |
| - | 0 | RE34649.URPN. | USPAT | 2001/05/18 08:34 |
| - | 9 | ("Re32893" \| "4796067" \| "4822992" \| "4894526" \| "4903101" \| "5010517" \| "5036371" \| "5121181" \| "5185647").PN. | USPAT | 2001/05/18 08:35 |
| - | 16 | ("4203124" \| "4383269" \| "4390889" \| "4471370" \| "4587544" \| "4616241" \| "4631566" \| "4711857" \| "4712121" \| "4722907" \| "4739385" \| "4761680" \| "4814837" \| "4826295" \| "4851886" \| "4903101").PN. | USPAT | 2001/05/18 08:35 |
| - | 896 | (("257/17,21,185").CCLS.) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/26 14:36 |
| - | 9 | composition with gradient and ((("257/17,21,185").CCLS.) ) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/10/09 14:56 |
| - | 47 | composition with gradient with transfer | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/10/09 15:23 |
| - | 4 | composition with gradient with transfer and (438/$ 257/$) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/10/09 15:45 |
| - | 2 | ((AlGaAs "Al Ga As" "AlGaAs" "Al.sub.0.44 Ga.sub.0.56 As" "Al.sub.0.22 Ga.sub.0.78 As") and ("Ga As" "GaAs" GaAs) and (InGaAs "In Ga As" "InGaAs" "In.sub.0.44 Ga.sub.0.56 As" "In.sub.0.15 Ga.sub.0.85 As")) same composition with gradient | USPAT | 2001/10/09 15:44 |

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|---|---:|---|---|---|
| - | 5 | composition with grad$4 with transfer and (438/$ 257/$) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/10/09 15:54 |
| - | 77 | composition with grad$4 with barrier and (438/$ 257/$) not (composition with grad$4 with transfer and (438/$ 257/$)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/10/10 09:03 |
| - | 23 | (composition with grad$4 with barrier and (438/$ 257/$) not (composition with grad$4 with transfer and (438/$ 257/$))) and III-V | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/10/09 16:37 |
| - | 54 | (composition with grad$4 with barrier and (438/$ 257/$) not (composition with grad$4 with transfer and (438/$ 257/$))) not ((composition with grad$4 with barrier and (438/$ 257/$) not (composition with grad$4 with transfer and (438/$ 257/$))) and III-V) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/10/09 16:38 |
| - | 22 | DEVEAUD-PLEDRAN-B DEVEAUD-PLEDRAN-BENOIT DEVEAUD-PLEDRAN-ET-AL DEVEAUD-PLEDRAN | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/10/10 09:14 |
| - | 36 | VINTER-BORGE VINTER-ET-AL | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/10/10 09:14 |
| - | 22 | VINTER-BORGE | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/10/10 11:48 |
| - | 1 | ("5432362").PN. | USPAT | 2001/10/10 09:25 |
| - | 1 | ("5311211").PN. | USPAT | 2001/10/10 09:25 |
| - | 1 | ("5311221").PN. | USPAT | 2001/10/10 09:27 |
| - | 2250 | decreas$3 with (emitt$3 near8 collect$3) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/10/10 09:30 |
| - | 41 | decreas$3 with (emitt$3 near8 collect$3) with (band adj gap energy) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/10/10 10:01 |
| - | 80 | ROSENCHER-EMMANUEL ROSENCHER-ET-AL ROSENCHER | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/10/10 10:07 |
| - | 10 | (VINTER-BORGE VINTER-ET-AL) and (ROSENCHER-EMMANUEL ROSENCHER-ET-AL ROSENCHER) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/10/10 10:07 |

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|---|---:|---|---|---|
| - | 2 | ohmic adj contact$1 with electron adj storage adj layer | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2001/10/10 13:53 |
| - | 1 | ("5429957").PN. | USPAT | 2001/10/10 13:53 |
| - | 921 | (257/17,21,185).CCLS. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/02/13 16:46 |
| - | 594 | well$1 and ((257/17,21,185).CCLS.) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/02/13 16:46 |
| - | 422 | barrier and (well$1 and ((257/17,21,185).CCLS.)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/02/13 16:48 |
| - | 422 | (barrier and (well$1 and ((257/17,21,185).CCLS.))) and pd@>=20011009 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/02/13 16:48 |
| - | 14 | (barrier and (well$1 and ((257/17,21,185).CCLS.))) and @pd>=20011009 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/02/13 16:49 |
| - | 0 | BERGER-VINCANT BERGER-VINCENT | US-PGPUB | 2002/09/26 13:38 |
| - | 0 | BERGER-VINCANT BERGER-VINCENT | US-PGPUB | 2002/09/26 13:39 |
| - | 19 | BERGER-VINCANT BERGER-VINCENT | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/26 13:53 |
| - | 0 | 967662.URPN. | USPAT | 2002/09/26 13:44 |
| - | 4 | BERGER-VINCANT BERGER-VINCENT BERGER-V | USPAT; US-PGPUB | 2002/09/26 13:54 |
| - | 0 | BERGER-VINCANT BERGER-VINCENT BERGER-V | US-PGPUB | 2002/09/26 13:54 |
| - | 973 | (("257/17,21,185").CCLS.) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/26 14:36 |
| - | 44 | ((("257/17,21,185").CCLS.) ) and @pd>=20020213 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/14 11:34 |
| - | 13 | ((("257/17,21,185").CCLS.) ) and @pd>=20020926 and barrier and well | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/14 11:36 |
| - | 1 | transfer near barrier with (angstrom ang nm nanometer nano micron micrometer micro thick thickness) same quantum near well with (angstrom ang nm nanometer nano micron micrometer micro thick thickness) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/06 09:19 |

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|---|---|---|---|---|
| - | 1648 | barrier with (angstrom ang nm nanometer nano micron micrometer micro thick thickness) same quantum near well with (angstrom ang nm nanometer nano micron micrometer micro thick thickness) not (transfer near barrier with (angstrom ang nm nanometer nano micron micrometer micro thick thickness) same quantum near well with (angstrom ang nm nanometer nano micron micrometer micro thick thickness)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/06 09:29 |
| - | 2759 | (257/11,189,200,201,615,745,e31.019,e31.026,e31.059,e33.049,e33.023,e33.037,3e7.089,e27.012).CCLS | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/06 09:31 |
| - | 64 | (barrier with (angstrom ang nm nanometer nano micron micrometer micro thick thickness) same quantum near well with (angstrom ang nm nanometer nano micron micrometer micro thick thickness) not (transfer near barrier with (angstrom ang nm nanometer nano micron micrometer micro thick thickness) same quantum near well with | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/06 14:33 |

(angstrom ang nm nanometer nano micron micrometer micro thick thickness))) and ((257/11,189,200,201,615,745,e31.019,e31.026,e31.059,e33.049,e33.023,e33.037,3e7.089,e27.012).CCL

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|---|---|---|---|---|
| 1 | 2 | ("5955772").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/06 14:34 |
| 3 | 0 | (transfer near barrier with (angstrom ang nm nanometer nano micron micrometer micro thick thickness)) same quantum near well with (angstrom ang nm nanometer nano micron micrometer micro thick thickness) and ((257/17,21,85).CCLS.) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/06 14:47 |